TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

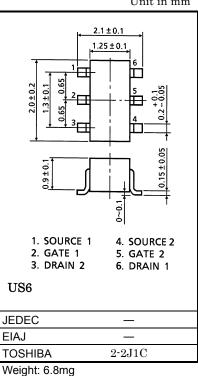
# HN1K03FU

### High Speed Switching Applications Analog Switch Applications

- Hign input impedance •
- Low gate threshold voltage  $: V_{th} = 0.5 V \sim 1.5 V$ •
- Excellent switching times  $: t_{on} = 0.16 \mu s$  (typ.)
  - $t_{off} = 0.15 \mu s$  (typ.)
- Small package
- Enhancement-mode

#### Absolute Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristic	Symbol	Rating	Unit
Drain-Source voltage	V <sub>DS</sub>	20	V
Gate-Source voltage	V <sub>GSS</sub>	10	V
DC Drain current	۱ <sub>D</sub>	100	mA
Drain power dissipation	P <sub>D</sub> *	200	mW
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C



Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

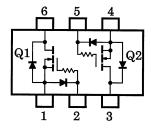
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

\*: Total rating Unit in mm

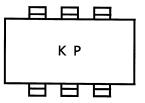
### Electrical Characteristics (Ta = 25°C) (Q1, Q2 Common)

Chara	cteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Gate leakage cu	rrent	I <sub>GSS</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 0	_	—	1	μA
Drain-Source bre	eakdown voltage	V (BR) DSS	I <sub>D</sub> = 100μA, V <sub>GS</sub> = 0	20	_	_	V
Drain cut-off cur	rent	I <sub>DSS</sub>	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0	_	_	1	μA
Gate threshold v	oltage	V <sub>th</sub>	V <sub>DS</sub> = 3V, I <sub>D</sub> = 0.1mA	0.5	_	1.5	V
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 3V, I <sub>D</sub> = 10mA	25	50	_	mS
Drain-Source ON resistance		R <sub>DS (ON)</sub>	I <sub>D</sub> = 10mA, V <sub>GS</sub> = 2.5V	_	8	12	Ω
Input capacitance	e	C <sub>iss</sub>	$V_{DS} = 3V, V_{GS} = 0, f = 1MHz$	_	8.5	_	pF
Reverse transfer	capacitance	C <sub>rss</sub>	$V_{DS} = 3V, V_{GS} = 0, f = 1MHz$		3.3	—	pF
Output capacitance		C <sub>oss</sub>	$V_{DS} = 3V, V_{GS} = 0, f = 1MHz$	_	9.3	_	pF
Switching time	Turn-on time	t <sub>on</sub>	V <sub>DD</sub> = 3V, I <sub>D</sub> = 10mA, V <sub>GS</sub> = 0~2.5V		0.16	_	μs
	Turn-off time	t <sub>off</sub>	V <sub>DD</sub> = 3V, I <sub>D</sub> = 10mA, V <sub>GS</sub> = 0~2.5V		0.15	_	μs

## Equivalent Circuit (Top View)



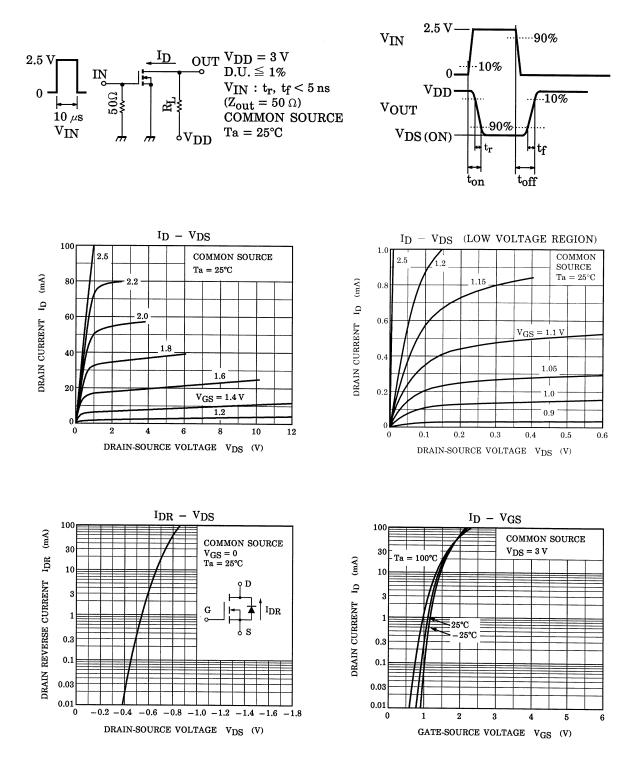
### Marking



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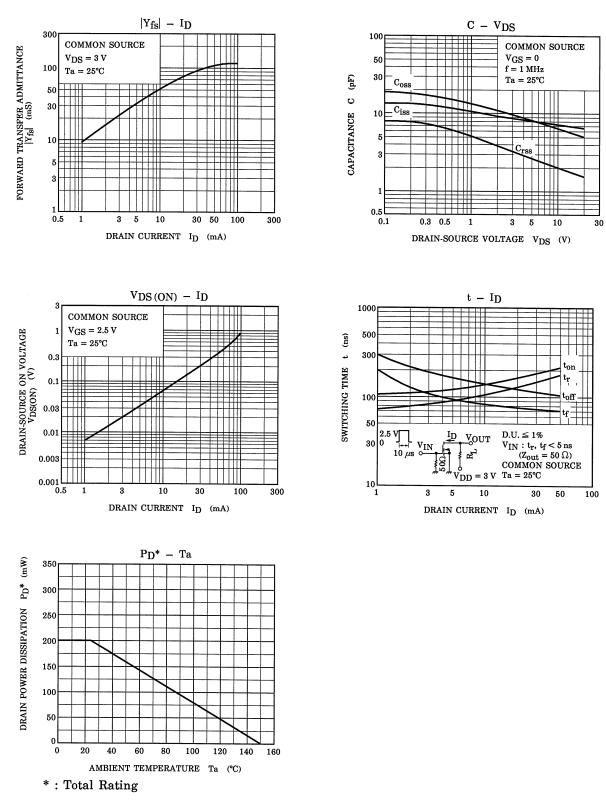
### (Q1,Q2 Common)

### Switching Time Test Circuit



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#### (Q1,Q2 Common)



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20070701-EN GENERAL

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